**IN THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a semiconductor thin film over a substrate having an insulating surface; and

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer;

wherein the first conductive layer has a larger width than the second conductive layer, and

wherein the transparent conductive film is on ~~in contact with~~ a part of the first conductive film extending from an end portion of the second conductive layer.

2. (Currently Amended) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a semiconductor thin film over a substrate having an insulating surface; and

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer;

wherein the first conductive layer has a portion projected from an end portion of the second conductive layer, and

wherein the transparent conductive film is on ~~in contact with~~ the portion of the first conductive film projected from the end portion of the second conductive layer.

3. (Currently Amended) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a semiconductor thin film over a substrate having an insulating surface; and

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer;

wherein a side surface portion of the first conductive layer has a smaller tapered angle than a side surface portion of the second conductive layer, and

wherein the transparent conductive film is on ~~in contact with~~ the side surface portion of the first conductive layer.

4. (Currently Amended) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a semiconductor thin film over a substrate having an insulating surface; and

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer;

wherein a side surface portion of the first conductive layer has a larger tapered angle than a side surface portion of the second conductive layer, and

wherein the transparent conductive film is on ~~in contact with~~ the side surface portion of the first conductive layer.

5. (Currently Amended) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a

semiconductor thin film over a substrate having an insulating surface; and

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer;

wherein a side surface portion of the first conductive layer and the second conductive layer have a same tapered angle, and

wherein the transparent conductive film is <u>on</u> ~~in contact with~~ the side surface portion of the first conductive layer.

6. (Original) A semiconductor device comprising:

a transparent conductive film and a plurality of thin film transistors having a semiconductor thin film over a substrate having an insulating surface;

an electrode or a wiring formed by stacking a first conductive layer in contact with the semiconductor thin film and a second conductive layer on the first conductive layer; and

a flattening insulating film over a part of the electrode or a part of the wiring;

wherein the transparent conductive film is provided over the flattening insulating film,

wherein the first conductive layer has a portion projected from an end portion of the second conductive layer,

wherein the electrode or the wiring is in contact with the transparent conductive film through a contact hole provided in the flattening insulating film, and

wherein an end portion of the electrode or an end portion of the wiring is located within the contact hole.

7. (Original) The semiconductor device according to any one of Claims 1 to 6,

wherein the first conductive layer is formed with titanium, molybdenum, alloy containing titanium, or alloy containing molybdenum.

8. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[7]] 6,

wherein the second conductive layer is formed with aluminum or alloy containing aluminum.

9. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[8]] 6, further comprising:

a light-emitting element in which the transparent conductive film serves as an anode or a cathode.

10. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[8]] 6, further comprising:

a liquid crystal element in which the transparent conductive film serves as a pixel electrode.

11. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[10]] 6,

wherein the transparent conductive film is formed with ITO or IZO.

12. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[11]] 6,

wherein a surface of the second conductive layer is covered with an oxide film.

13. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[12]] 6,

wherein the first conductive layer and the second conductive layer are formed continuously in a same sputtering apparatus.

14. (Currently Amended) The semiconductor device according to any one of Claims 1 to [[13]] 6,

wherein the semiconductor device is a mobile information terminal, a video camera, a digital camera, or a personal computer.